

AMENDED CLAIM SET

The claims have been amended as set forth in the following listing of the claims:

1. [1]—(Currently Amended) A plasma processing apparatus, comprising:

gas supply means for supplying a gas including a reactant gas to an interior of a chamber;

pressure control means for controlling an internal pressure of the chamber;

plasma generation means for generating a plasma of the gas in the interior of the chamber; and

a susceptor, installed in a lower portion of the interior of the chamber, for supporting a substrate to be processed; to be processed, and

further comprising a wall surface protecting member, formed in a cylindrical form and  
provided in the interior of the chamber, for preventing adhesion of a plasma processing-associated product onto an inner wall surface of the chamber,

wherein the chamber includes a chamber step portion, provided to the inner wall surface of the chamber, for supporting the wall surface protecting member from below to cover the inner wall surface of the chamber located above the susceptor,

wherein the wall surface protecting member has a plurality of projections, provided on an outer wall surface and in a lower end portion of the wall surface protecting member, for contacting, by point contact, the inner wall surface of the chamber and the chamber step portion, and

wherein the wall surface protecting member is supported in the chamber by the point contact.

2. (Canceled)

3. (Canceled)

4. [4] (Currently Amended) The plasma processing apparatus according to claim 1, wherein characterized in that the wall surface protecting member is made of a ceramic.

5. [5] (Currently Amended) The plasma processing apparatus according to claim 1, wherein claim, 1, characterized in that the wall surface protecting member is made of a metal.

6. [6] (Currently Amended) The plasma processing apparatus according to claim 5, wherein eharacterized in that the metal is aluminum.

7. [7] (Currently Amended) The plasma processing apparatus according to claim 5, wherein eharacterized in that the wall surface protecting member has a surface oxidized.

8. [8] (Currently Amended) The plasma processing apparatus according to claim 1, wherein eharacterized in that the wall surface protecting member has a surface roughened.

9. [9] (Currently Amended) The plasma processing apparatus according to claim 1, wherein characterized in that the gas supply means is installed while passing through a hole provided in the wall surface protecting member.

10. (Canceled)

11. [11]—(Currently Amended) The plasma processing apparatus according to claim 1, further comprising:

heating means for heating a wall surface of the chamber.

12. [12]—(Currently Amended) The plasma processing apparatus according to claim 11, wherein characterized in that the heating means heats the wall surface of the chamber to 100°C or higher.